



Docket No.: M4065.0151/P151-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Vishnu K. Agarwal, et al.

Application No.: 09/930,958

Group Art Unit: 2814

Filed: August 17, 2001

Examiner: Theresa T. Doan

For: MULTILAYER ELECTRODE FOR A
FERROELECTRIC CAPACITOR

#78 Jut
M. Brunson
2/12/03

AMENDMENT

BOX: NON-FEE AMENDMENT

Commissioner for Patents
Washington, DC 20231

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TECHNOLOGY CENTER 2800

Dear Sir:

Responsive to the Office Action dated November 4, 2002, please amend the
above-captioned application as follows:

IN THE CLAIMS:

Please cancel claims 56, 59, 61-62 and 72-123.

Please rewrite claims 55 and 60.

55. (amended) A memory cell, comprising:

a substrate;

a transistor including a gate on said substrate and a source/drain region in said
substrate disposed adjacent to said gate;

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D1